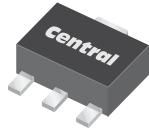


CXTA14 NPN  
CXTA64 PNP

**SURFACE MOUNT  
COMPLEMENTARY SILICON  
DARLINGTON TRANSISTORS**



**SOT-89 CASE**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CXTA14, CXTA64 types are complementary silicon Darlington transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	SYMBOL		UNITS
Collector-Base Voltage	$V_{CBO}$	30	V
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Base Voltage	$V_{EBO}$	10	V
Continuous Collector Current	$I_C$	500	mA
Power Dissipation	$P_D$	1.2	W
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$	104	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=30\text{V}$		100	nA
$I_{EBO}$	$V_{EB}=10\text{V}$		100	nA
$BV_{CES}$	$I_C=100\mu\text{A}$	30		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=0.1\text{mA}$		1.5	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$		2.0	V
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	10,000		
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$	20,000		
$f_T$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	125		MHz

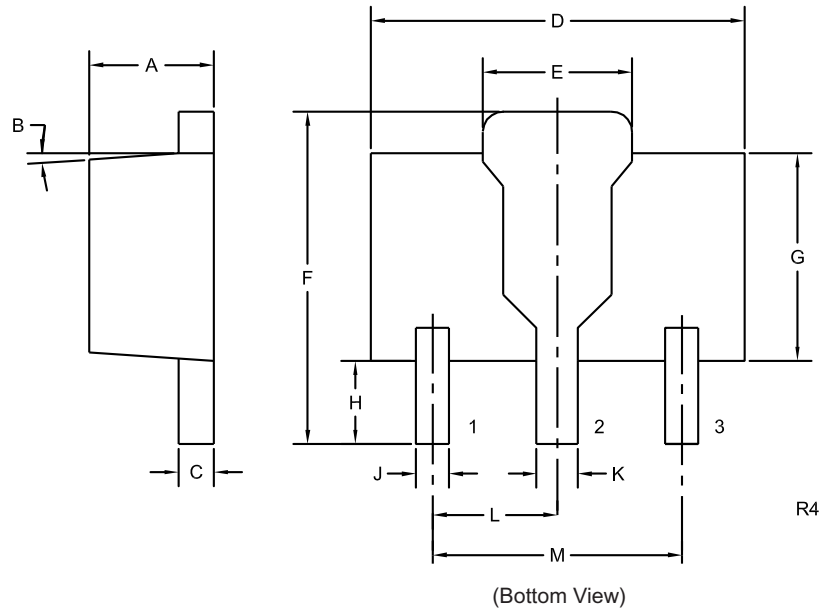
R6 (23-February 2010)

CXTA14 NPN  
 CXTA64 PNP

**SURFACE MOUNT  
 COMPLEMENTARY SILICON  
 DARLINGTON TRANSISTORS**



**SOT-89 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**

- 1) Emitter
- 2) Collector
- 3) Base

**MARKING:  
 FULL PART NUMBER**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.067	1.40	1.70
B	4°		4°	
C	0.014	0.018	0.35	0.46
D	0.173	0.185	4.40	4.70
E	0.064	0.074	1.62	1.87
F	0.146	0.177	3.70	4.50
G	0.090	0.106	2.29	2.70
H	0.028	0.051	0.70	1.30
J	0.014	0.019	0.36	0.48
K	0.017	0.023	0.44	0.58
L	0.059		1.50	
M	0.118		3.00	

SOT-89 (REV: R4)

R6 (23-February 2010)